

Amendments to the Specification

Next, a second conductive layer 150, such as polycrystalline silicon (often referred to as a "Poly 2" layer) can be uniformly formed over the HTO or top dielectric layer 52 in the core area 14 and over the already-existing first conductive layer 110 in the periphery area 16, as shown. The second conductive layer ~~180~~ 150 can also be made from, for example, another appropriate material, such as a metal or metal containing compound. In one embodiment, a second polysilicon layer 150 can be deposited using, for example, LPCVD techniques as are known. In one embodiment, the second conductive layer 150 can have thickness greater than the first conductive layer 110 (e.g., between about 900 angstroms and about 3000 angstroms).